

3DK29-II, 3DK29**NPN Silicon High Frequency Low-Middle Power Switch Transistor****Features:**

1. Using epitaxy planar technology structure. High working frequency. Metallic packaging.
2. Small volume, light weight, easy installation.
3. Use for high frequency oscillation and high frequency switch, high frequency small signal amplification, low power source adjustment circuit.
4. Quality Class: GS, G. Implementation of standards: QZJ840611

TECHNICAL DATA:**(Ta = 25°C)**

Parameter name	Symbols	Unit	Specifications								
			3DK29-II					3DK29			
			A	B	C	D	E	A	B	C	D
Total Dissipation	P_{tot}	mW	1000 (Ta=25°C)					100 (Ta=25°C)			
Max. Collector Current	I_{CM}	mA	1000					500			
Junction Temperature	T_{jm}	°C	175								
Storage Temperature	T_{stg}	°C	-55~+175								
C-B Breakdown Voltage	$V_{(BR)CBO}$	V	40	60	75	60	40	25	40	25	40
			Ic=0.1mA								
C-E Breakdown Voltage	$V_{(BR)CEO}$	V	30	45	60	45	30	15	30	15	30
			Ic=0.1mA								
E-B Breakdown Voltage	$V_{(BR)EBO}$	V	≥4 (I _E =0.1 mA)								
Collector- Emitter Saturation Voltage Drop	$V_{CE(sat)}$	V	0.4					0.5			
			(I _C =500mA, I _B =50mA)					(I _C =300mA, I _B =30mA)			
Base- Emitter Saturation Voltage Drop	$V_{BE(sat)}$	V	1.2					1.2			
			(I _C =500mA, I _B =50mA)					(I _C =300mA, I _B =30mA)			
C-E Leakage Current	I_{CEO}	uA	1.0 (V _{CE} =20V)					2.0 (V _{CE} =10V)			
DC Current Gain	h_{FE}		Orange:25~40, Yellow:40~55, Green:55~80, Blue:80~120, Purple:120~180								
			(V _{CE} =1V, I _C =500mA)					(V _{CE} =1V, I _C =300mA)			
Transition frequency	f_T	MHz	150 (V _{CE} =10V, I _C =50mA, f=30MHz)					400 (V _{CE} =10V, I _C =50mA, f=100MHz)			
Turn-on Time	I _C =300 mA I _{B1} = I _{B2} =30mA	t_{on}	30					15			
Storage Time		t_s	250		100			30			
Fall Time		t_f	30					10			

Outline and Dimensions: